# LL101A...LL101C

Silicon Schottky Barrier Diodes

for general purpose applications

The LL101 Series is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

This diode is also available in DO-35 case with type designation SD101A, B, C.

LL-34

3.5+/-0.1

∅1.45+/-0.05

Cathode Mark

0.3+/-0.1
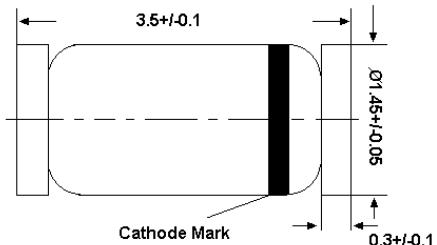
Glass case MiniMELF

Dimensions in mm

Absolute Maximum Ratings (T_a = 25 ^{o}C)

Parameter		Symbol	Value	Unit
Peak Reverse Voltage LL101A LL101B LL101C		V_{RRM}	60 50 40	V
Maximum Single Cycle Surge 10 µs Square Wave		I_{FSM}	2	A
Power Dissipation (Infinite Heatsink)		P_{tot}	400 [1]	mW
Junction Temperature		T_j	200	^{o}C
Storage Temperature Range		T_{stg}	- 55 to + 200	^{o}C
[1] Valid provided that electrodes are kept at ambient temperature.				

Characteristics at T_a = 25 ^{o}C

| Parameter		Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 10 µA LL101A LL101B LL101C		$V_{(BR)R}$	60 50 40	- - -	V
Forward Voltage at I_F = 1 mA at I_F = 15 mA 	LL101A LL101B LL101C LL101A LL101B LL101C	V_F	- - - - - -	0.41 0.4 0.39 1 0.95 0.9	V
Reverse Current at V_R = 50 V LL101A at V_R = 40 V LL101B at V_R = 30 V LL101C		I_R	- - -	200 200 200	nA
Junction Capacitance at V_R = 0 V, f = 1 MHz LL101A LL101B LL101C		C_{tot}	- - -	2.0 2.1 2.2	pF
Reverse Recovery Time at I_F = I_R = 5 mA , recover to 0.1 I_R		t_{rr}	-	1	ns

**Typical variation of fwd. current
vs. fwd. voltage for primary conduction
through the Schottky barrier**
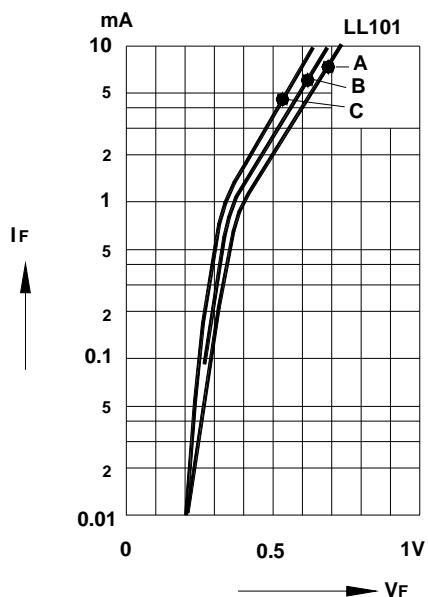
**Typical forward conduction curve
of combination Schottky barrier
and PN junction guard ring**
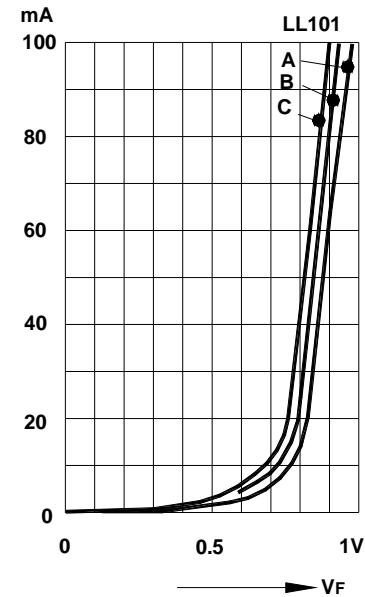
**Typical variation of reverse current
at various temperatures**
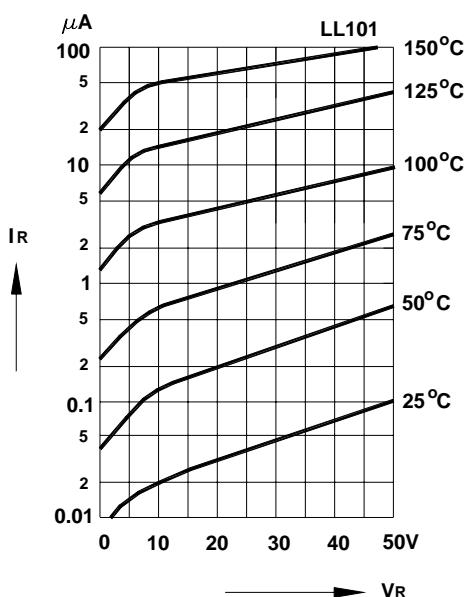
**Typical capacitance curve as a
function of reverse voltage**

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